Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

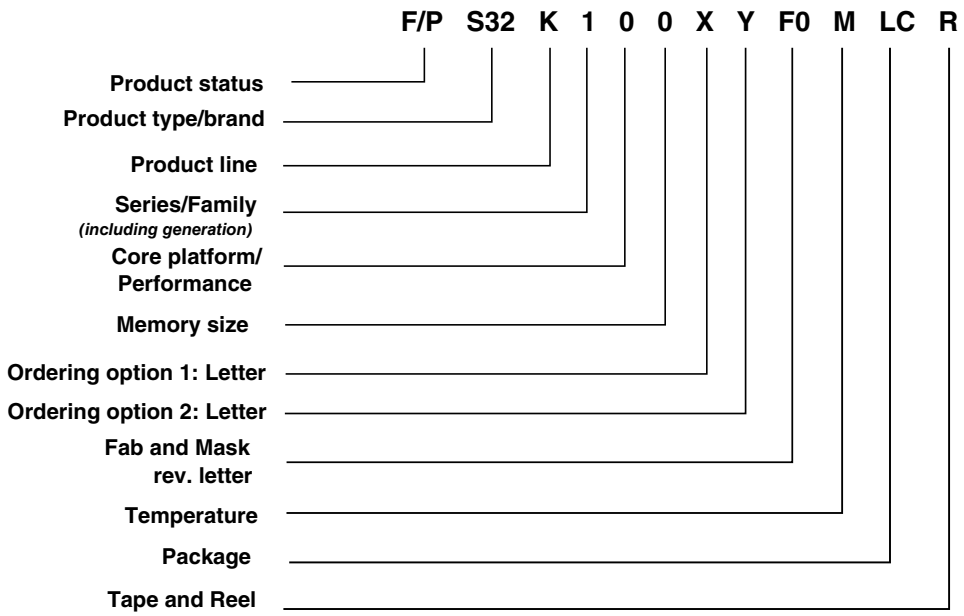
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	112MHz
Connectivity	CANbus, FlexIO, I²C, LINbus, SPI, UART/USART
Peripherals	POR, PWM, WDT
Number of I/O	58
Program Memory Size	512KB (512K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 16x12b SAR; D/A1x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 125°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/fs32k144uat0mlht

- Reliability, safety and security
  - HW Security Engine (CSEc)
  - Internal watchdog (WDOG)
  - External Watchdog monitor (EWM) module
  - Error-Correcting Code (ECC) on flash and SRAM memories
  - Cyclic Redundancy Check (CRC) module
  - 128-bit Unique Identification (ID) number
  - System Memory Protection Unit (System MPU)
- Timing and control
  - Up eight independent 16-bit FlexTimers (FTM) module, offering up to 64 standard channels (IC/OC/PWM)
  - One 16-bit Low Power Timer (LPTMR) with flexible wake up control
  - Two Programmable Delay Blocks (PDB) with flexible trigger system
  - One 32-bit Low Power Interrupt Timer (LPIT) with 4 channels
  - 32-bit Real Time Counter (RTC)
- I/O and package
  - 32-pin QFN, 48-pin LQFP, 64-pin LQFP, 100-pin LQFP, MAPBGA-100, 144-pin LQFP, 176-pin LQFP package options
- 16 channel DMA with up to 63 request sources using DMAMUX

Table of Contents

3.2 Ordering information



Product status
P: Prototype
F: Qualified ordering P/N

Product type/brand
S32: Automotive 32-bit MCU

Product line
K: ARM Cortex MCUs
M: MagniV/Mixed Signal

Series/Family
1: 1st product series
2: 2nd product series

Core platform/Performance
1: ARM Cortex M0+
4: ARM Cortex M4F

Memory size

	2	4	6	8
M0+	32 K	64 K	128 K	256 K
M4F	256 K	512 K	1 M	2 M

Ordering option
X: Speed
B: 48 MHz without DMA (only for S32K11x)
L: 48 MHz with DMA (only for S32K11x)
M: 64 MHz
H: 80 MHz
U: 112 MHz

Y: Optional feature
N: No/None
R: Max. RAM
F: CAN-FD and FlexIO including max. RAM
S: Security including max. RAM
A: CAN-FD, FlexIO, and Security including max. RAM
E: Ethernet and audio including max. RAM
J: CAN FD, FlexIO, Security, Ethernet and audio including max. RAM

Fab and Mask rev. letter
Fx: ATMC
Tx: GF
XX: Flex #

x0: 1st fab revision
x1: 2nd fab revision

Temperature
C: -40C to 85C
V: -40C to 105C
M: -40C to 125C

Package

Pins	LQFP	LQFP -EP	QFN	BGA
32	LC	-	FM	-
48	LF	KF	FT	-
64	LH	KH	-	-
100	LL	-	-	MH
144	LQ	-	-	-
176	LU	-	-	-

Tape and Reel
T: Trays and Tubes
R: Tape and Reel

Figure 4. Ordering information

4 General

4.1 Absolute maximum ratings

NOTE

Functional operating conditions appear in the DC electrical characteristics. Absolute maximum ratings are stress ratings only, and functional operation at the maximum values is not guaranteed. See footnotes in the following table for specific conditions.

Stress beyond the listed maximum values may affect device reliability or cause permanent damage to the device.

All the limits defined in the datasheet specification must be honored together and any volilation to any one or more will not gaurantee desired operation.

Table 1. Absolute maximum ratings

Symbol	Parameter	Conditions[1]	Min	Max	Unit
V_{DD}[2]	2.7 V - 5. 5V input supply voltage	—	-0.3	5.8 [3]	V
V_{REFH}	3.3 V / 5.0 V ADC high reference voltage	—	-0.3	5.8 [3]	V
$I_{INJPAD\_DC\_ABS}$[4]	Continuous DC input current (positive / negative) that can be injected into an I/O pin	—	-3	+3	mA
V_{IN_DC}	Continuous DC Voltage on any I/O pin with respect to V_{SS}	—	-0.8	5.8[5]	V
$I_{INJSUM\_DC\_ABS}$	Sum of absolute value of injected currents on all the pins (Continuous DC limit)	—	—	30	mA
T_{ramp}[6]	Supply ramp rate	—	0.5 V/min	500 V/ms	—
T_A[7]	Ambient temperature	—	-40	125	°C
T_{STG}	Storage temperature	—	-55	165	°C
$V_{IN\_TRANSIENT}$	Transient overshoot voltage allowed on I/O pin beyond $V_{IN\_DC\ limit}$	—	—	6.8 [8]	V

1. All voltages are referred to V_{SS} unless otherwise specified.
2. As V_{DD} varies between the minimum value and the absolute maximum value the analog characteristics of the I/O and the ADC will both change. See section I/O parameters and ADC electrical specifications respectively for details.
3. 60 s lifetime – No restrictions i.e. The part can switch.

   10 hours lifetime – Device in reset i.e. The part cannot switch.
4. When input pad voltage levels are close to V_{DD} or V_{SS}, practically no current injection is possible.
5. While respecting the maximum current injection limit
6. Limit applies to both maximum absolute maximum ramp rate and typical operating conditions.
7. T_J (Junction temperature)=135 °C. Assumes T_A=125 °C for RUN mode

T_J (Junction temperature)=125 °C. Assumes TA=105 °C for HSRUN mode

- Assumes maximum θJA for 2s2p board. See Thermal characteristics

8. 60 seconds lifetime; device in reset (no outputs enabled/toggling)

4.2 Voltage and current operating requirements

NOTE

Full functionality/specifications cannot be guaranteed when voltage drops below 2.7 V.

Table 2. Voltage and current operating requirements [1]

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}[2]	Supply voltage	2.7[3]	5.5	V	4
V_{DD_OFF}	Voltage allowed to be developed on V_{DD} pin when it is not powered from any external power supply source.	0	0.1	V	
V_{DDA}	Analog supply voltage	2.7	5.5	V	4
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	– 0.1	0.1	V	
V_{REFH}	ADC reference voltage high	2.7	V_{DDA} + 0.1	V	5
V_{REFL}	ADC reference voltage low	-0.1	0.1	V	
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	6
$I_{INJPAD\_DC\_OP}$[7]	Continuous DC input current (positive / negative) that can be injected into an I/O pin	-3	+3	mA	
$I_{INJSUM\_DC\_OP}$	Continuous total DC input current that can be injected across all I/O pins such that there's no degradation in accuracy of analog modules: ADC and ACMP (See section Analog Modules)	—	30	mA	

1. Typical conditions assumes V_{DD} = V_{DDA} = V_{REFH} = 5 V, temperature = 25 °C and typical silicon process unless otherwise stated.
2. As V_{DD} varies between the minimum value and the absolute maximum value the analog characteristics of the I/O and the ADC will both change. See section I/O parameters and ADC electrical specifications respectively for details.
3. S32K148 will operate from 2.7 V when executing from internal FIRC. When the PLL is engaged S32K148 is guaranteed to operate from 2.97 V. All other S32K family devices operate from 2.7 V in all modes.
4. V_{DD} and V_{DDA} must be shorted to a common source on PCB. Appropriate decoupling capacitors to be used to filter noise on the supplies. See application note AN5032 for reference supply design for SAR ADC.
5. V_{REFH} should always be equal to or less than V_{DDA} + 0.1 V and V_{DD} + 0.1 V
6. Open drain outputs must be pulled to V_{DD}.
7. When input pad voltage levels are close to V_{DD} or V_{SS}, practically no current injection is possible.

4.7.1 Modes configuration

Attached *S32K1xx_Power_Modes _Configuration.xlsx* details the modes used in gathering the power consumption data stated in the above table Table 7. For full functionality refer to table: Module operation in available low power modes of the *Reference Manual*.

4.8 ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	– 4000	4000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model				2
	All pins except the corner pins	– 500	500	V	
	Corner pins only	– 750	750	V	
I_{LAT}	Latch-up current at ambient temperature of 125 °C	– 100	100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

4.9 EMC radiated emissions operating behaviors

EMC measurements to IC-level IEC standards are available from NXP on request.

5 I/O parameters

5.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

6.3.1.1 Flash timing specifications — commands

Table 21. Flash command timing specifications

Symbol	Description[1]	Min.	Typ.	Max.	Unit	Notes
$t_{rd1blk64k}$ $t_{rd1blk512k}$	Read 1s Block execution time • 64 KB data flash • 512 KB program flash	— —	— —	0.5 1.8	ms ms	
$t_{rd1sec2k}$	Read 1s Section execution time (2 KB flash)	—	—	75	µs	
$t_{rd1sec4k}$	Read 1s Section execution time (4 KB flash)	—	—	100	µs	
t_{pgmchk}	Program Check execution time	—	—	95	µs	
t_{pgm8}	Program Phrase execution time	—	90	150	µs	
$t_{ersblk64k}$ $t_{ersblk512k}$	Erase Flash Block execution time • 64 KB data flash • 512 KB program flash	— —	55 435	475 3700	ms ms	2
t_{ersscr}	Erase Flash Sector execution time	—	15	115	ms	2
$t_{pgmsec1k}$	Program Section execution time (1KB flash)	—	5	—	ms	
$t_{rd1allx}$	Read 1s All Blocks execution time	— — —	— — —	2.2 4.4 6.6	ms ms ms	
t_{rdonce}	Read Once execution time	—	—	30	µs	
$t_{pgmonce}$	Program Once execution time	—	90	—	µs	
t_{ersall}	Erase All Blocks execution time	—	500	4200	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	35	µs	
$t_{ersallu}$	Erase All Blocks Unsecure execution time	—	500	4200	ms	2
$t_{pgmpart32k}$ $t_{pgmpart64k}$	Program Partition for EEPROM execution time • 32 KB EEPROM backup • 64 KB EEPROM backup (Non-Interleaved DFlash) • 64 KB EEPROM backup (Interleaved DFlash)	— —	70 71 250	— —	ms ms ms	3, 4
$t_{setramff}$ $t_{setram32k}$ $t_{setram48k}$ $t_{setram64k}$	Set FlexRAM Function execution time: • Control Code 0xFF • 32 KB EEPROM backup • 48 KB EEPROM backup • 64 KB EEPROM backup	— — — —	70 0.8 1.0 1.3	— 1.2 1.5 1.9	µs ms ms ms	3, 4
$t_{eewr8b32k}$ $t_{eewr8b48k}$ $t_{eewr8b64k}$	Byte-write to FlexRAM execution time: • 32 KB EEPROM backup • 48 KB EEPROM backup • 64 KB EEPROM backup	— — —	385 430 475	1700 1850 2000	µs µs µs	3, 4
$t_{eewr16b32k}$ $t_{eewr16b48k}$	16-bit write to FlexRAM execution time: • 32 KB EEPROM backup	— —	385 430	1700 1850	µs µs	3, 4

Table continues on the next page...

Table 21. Flash command timing specifications (continued)

Symbol	Description[1]	Min.	Typ.	Max.	Unit	Notes
$t_{eewr16b64k}$	• 48 KB EEPROM backup • 64 KB EEPROM backup	—	475	2000	µs	
$t_{eewr32bers}$	32-bit write to erased FlexRAM location execution time	—	360	2000	µs	
$t_{eewr32b32k}$ $t_{eewr32b48k}$ $t_{eewr32b64k}$	32-bit write to FlexRAM execution time: • 32 KB EEPROM backup • 48 KB EEPROM backup • 64 KB EEPROM backup	— — —	630 720 810	2000 2125 2250	µs µs µs	3, 4
$t_{quickwr}$	32-bit Quick Write execution time : Time from CCIF clearing (start the write) until CCIF setting (32-bit write complete, ready for next 32-bit write)					
	• 1st 32-bit write • 2nd through Next to Last (Nth-1) 32-bit write • Last (Nth) 32-bit write (time for write only, not cleanup)	— — —	200 150 200	550 550 550	µs µs µs	5, 6
$t_{quickwrClnup}$	Quick Write Cleanup execution time	—	—	(Number of Quick Writes) * 2.0	ms	7

1. All command times assumes 25 MHz or greater flash clock frequency (for synchronization time between internal/external clocks).
2. Maximum times for erase parameters based on expectations at cycling end-of-life.
3. For all EEPROM Emulation terms, the specified timing shown assumes previous record clean up has occurred. This may be verified by executing FCCOB Command 0x77, and checking FCCOB number 5 contents show 0x00 - No EEPROM issues detected.
4. 'First time' EERAM writes after a Reset or SETRAM may incur additional overhead for EEE cleanup, resulting in up to 2x the times shown.
5. For 'Typ.', only after the Nth write completes will any data will be valid. Emulated EEPROM record scheme cleanup overhead may occur after this point even after a brownout or reset. If power or reset occurs before the Nth write completes, the last valid record set will still be valid and the new records will be discarded.
6. Quick Write may take up to 550 µs as additional cleanup may occur when crossing sector boundaries.
7. Time for emulated EEPROM record scheme overhead cleanup. Automatically done after last (Nth) write completes, assuming still powered. Or via SETRAM cleanup execution command is requested at a later point.

NOTE

Under certain circumstances FlexMEM maximum times may be exceeded. In this case the user or application may wait, or assert reset to the FTFC macro to stop the operation.

6.3.1.2 Reliability specifications

Table 22. NVM reliability specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
When using as Program and Data Flash						

Table continues on the next page...

Table 22. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	—	—	years	
$n_{nvmcycp}$	Cycling endurance	1 K	—	—	cycles	2, 1
When using FlexMemory feature: FlexRAM as Emulated EEPROM						
$t_{nvmretee}$	Data retention	5	—	—	years	
$n_{nvmwree16}$ $n_{nvmwree256}$	Write endurance • EEPROM backup to FlexRAM ratio = 16 • EEPROM backup to FlexRAM ratio = 256	100 K 1.6 M	— —	— —	writes writes	3, 4, 5

1. Program and Erase for PFlash and DFlash are supported across product temperature specification in Normal Mode (not supported in HSRUN mode).
2. Cycling endurance is per DFlash or PFlash Sector.
3. FlexMemory write endurance specified for 16-bit and/or 32-bit writes to FlexRAM and is supported across standard temperature specification in Normal Mode (not supported in HSRUN mode). Greater write endurance may be achieved with larger ratios of EEPROM backup to FlexRAM.
4. For usage of any other EEE driver other than the FlexMemory feature, the endurance specification will fall back to the specified endurance value of the D-Flash specification (1 K).
5. EEE calculator tool is available at NXP web site to help estimate the maximum write endurance achievable at specific EEPROM/FlexRAM ratio. The “In Spec” portions of the online calculator refer to the NVM reliability specifications section of data sheet. This calculator is only applies to the FlexMemory feature.

6.3.2 QuadSPI AC specifications

The following table describes the QuadSPI electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.
- Add 50 ohm series termination on board in QuadSPI SCK for Flash A to avoid loop back reflection when using in Internal DQS (PAD Loopback) mode.
- For non-Quad mode of operation if external device doesn’t have pull-up feature, external pull-up needs to be added at board level for non-used pads.
- With external pull-up, performance of the interface may degrade based on load associated with external pull-up.

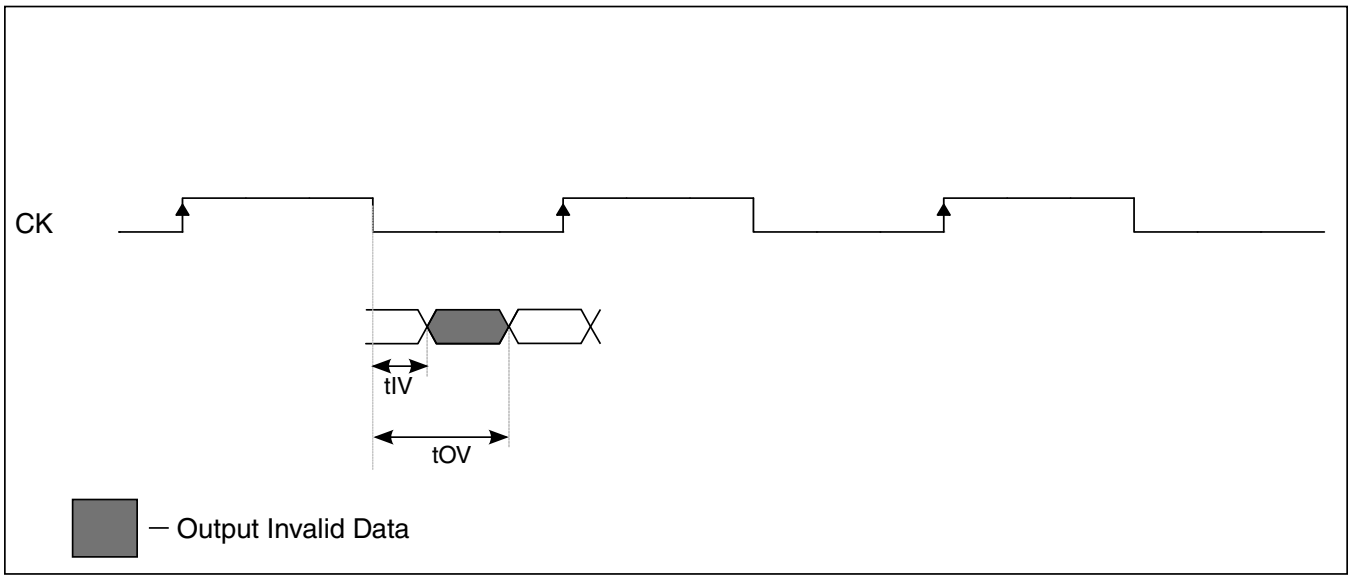


Figure 12. QuadSPI output timing (HyperRAM mode) diagram

6.4 Analog modules

6.4.1 ADC electrical specifications

6.4.1.1 12-bit ADC operating conditions

Table 24. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD} – V_{DDA})	-0.1	0	+0.1	V	2
V_{REFH}	ADC reference voltage high		See Voltage and current operating requirements for values	V_{DDA}	See Voltage and current operating requirements for values	V	3
V_{REFL}	ADC reference voltage low		See Voltage and current operating requirements for values	0	See Voltage and current operating requirements for values	mV	3
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
R_S	Source impedendance	f_{ADCK} < 4 MHz	—	—	5	kΩ	
R_{SW1}	Channel Selection Switch Impedance		—	-0.75	1.2	kΩ	
R_{AD}	Sampling Switch Impedance		—	2	5	kΩ	
C_{P1}	Pin Capacitance		—	10	—	pF	

Table continues on the next page...

Table 24. 12-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
C_{P2}	Analog Bus Capacitance		—	—	4	pF	
C_S	Sampling capacitance		—	4	5	pF	
f_{ADCK}	ADC conversion clock frequency	Normal usage	2	40	50	MHz	4, 5
f_{CONV}	ADC conversion frequency	No ADC hardware averaging.[6] Continuous conversions enabled, subsequent conversion time	46.4	928	1160	Ksps	7, 8
		ADC hardware averaging set to 32. [6] Continuous conversions enabled, subsequent conversion time	1.45	29	36.25	Ksps	7, 8

1. Typical values assume V_{DDA} = 5 V, Temp = 25 °C, f_{ADCK} = 40 MHz, R_{AS}=20 Ω, and C_{AS}=10 nF unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. For packages without dedicated V_{REFH} and V_{REFL} pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to V_{SS}. To get maximum performance, reference supply quality should be better than SAR ADC. See application note AN5032 for details.
4. Clock and compare cycle need to be set according to the guidelines mentioned in the *Reference Manual* .
5. ADC conversion will become less reliable above maximum frequency.
6. When using ADC hardware averaging, see the *Reference Manual* to determine the most appropriate setting for AVGS.
7. Numbers based on the minimum sampling time of 275 ns.
8. For guidelines and examples of conversion rate calculation, see the *Reference Manual* or download the ADC calculator tool.

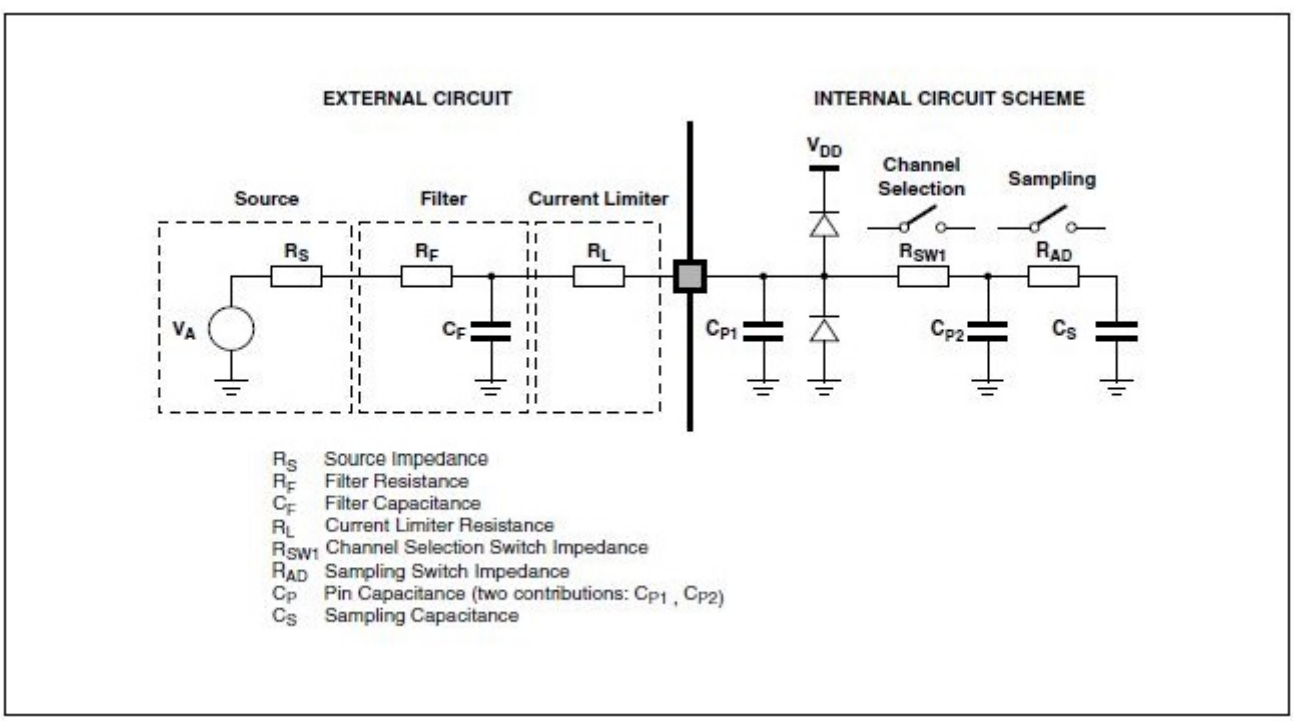


Figure 13. ADC input impedance equivalency diagram

Table 26. 12-bit ADC characteristics (3 V to 5.5 V)(V_{REFH} = V_{DDA}, V_{REFL} = V_{SS}) (continued)

Symbol	Description	Conditions [1]	Min.	Typ.[2]	Max.	Unit	Notes
TUE[4]	Total unadjusted error		—	±4	±8	LSB[5]	6, 7, 8, 9
DNL	Differential non-linearity		—	±0.7	—	LSB[5]	6, 7, 8, 9
INL	Integral non-linearity		—	±1.0	—	LSB[5]	6, 7, 8, 9

1. All accuracy numbers assume the ADC is calibrated with V_{REFH}=V_{DDA}=V_{DD}, with the calibration frequency set to half the ADC clock frequency.
2. Typical values assume V_{DDA} = 5.0 V, Temp = 25 °C, f_{ADCK} = 40 MHz, R_{AS}=20 Ω, and C_{AS}=10 nF unless otherwise stated.
3. The ADC supply current depends on the ADC conversion rate.
4. Represents total static error, which includes offset and full scale error.
5. 1 LSB = (V_{REFH} - V_{REFL})/2^N
6. The specifications are with averaging and in standalone mode only. Performance may degrade depending upon device use case scenario. When using ADC averaging, refer to the *Reference Manual* to determine the most appropriate settings for AVGS.
7. For ADC signals adjacent to V_{DD}/V_{SS} or XTAL/EXTAL or high frequency switching pins, some degradation in the ADC performance may be observed.
8. All values guarantee the performance of the ADC for multiple ADC input channel pins. When using ADC to monitor the internal analog parameters, assume minor degradation.
9. All the parameters in the table are given assuming system clock as the clocking source for ADC.

NOTE

When using high speed interfaces such as the QuadSPI, SAI0, SAI1 or ENET there may be some ADC degradation on the adjacent analog input paths. See following table for details.

Pin name	TGATE purpose
PTE8	CMP0_IN3
PTC3	ADC0_SE11/CMP0_IN4
PTC2	ADC0_SE10/CMP0_IN5
PTD7	CMP0_IN6
PTD6	CMP0_IN7
PTD28	ADC1_SE22
PTD27	ADC1_SE21

6.4.2 CMP with 8-bit DAC electrical specifications

Table 28. Comparator with 8-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DDHS}	Supply current, High-speed mode[1]				µA
	-40 - 125 °C	—	230	300	
I_{DDLS}	Supply current, Low-speed mode[1]				µA
	-40 - 105 °C	—	5	10	
	-40 - 125 °C		5	13	

Table continues on the next page...

Table 28. Comparator with 8-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DAC8b}	8-bit DAC current adder (enabled)				
	3.3V Reference Voltage	—	6	9	µA
	5V Reference Voltage	—	10	16	µA
INL[5]	8-bit DAC integral non-linearity	–0.75	—	0.75	LSB[6]
DNL	8-bit DAC differential non-linearity	–0.5	—	0.5	LSB[6]
t_{DDAC}	Initialization and switching settling time	—	—	30	µs

1. Difference at input > 200mV
2. Applied ± (100 mV + $V_{HYST0/1/2/3}$+ max. of V_{AIO}) around switch point.
3. Applied ± (30 mV + 2 × $V_{HYST0/1/2/3}$+ max. of V_{AIO}) around switch point.
4. Applied ± (100 mV + $V_{HYST0/1/2/3}$).
5. Calculation method used: Linear Regression Least Square Method
6. 1 LSB = $V_{reference}$/256

NOTE

For comparator IN signals adjacent to V_{DD}/V_{SS} or XTAL/EXTAL or switching pins cross coupling may happen and hence hysteresis settings can be used to obtain the desired comparator performance. Additionally, an external capacitor (1nF) should be used to filter noise on input signal. Also, source drive should not be weak (Signal with < 50 K pull up/down is recommended).

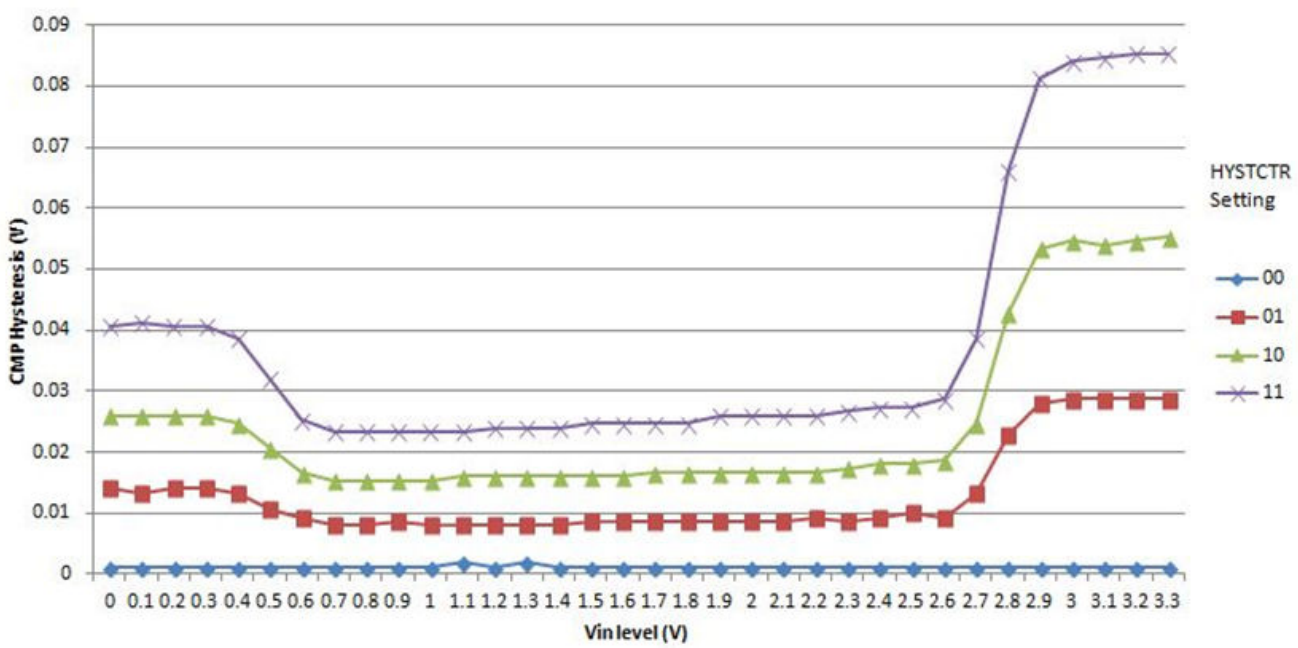
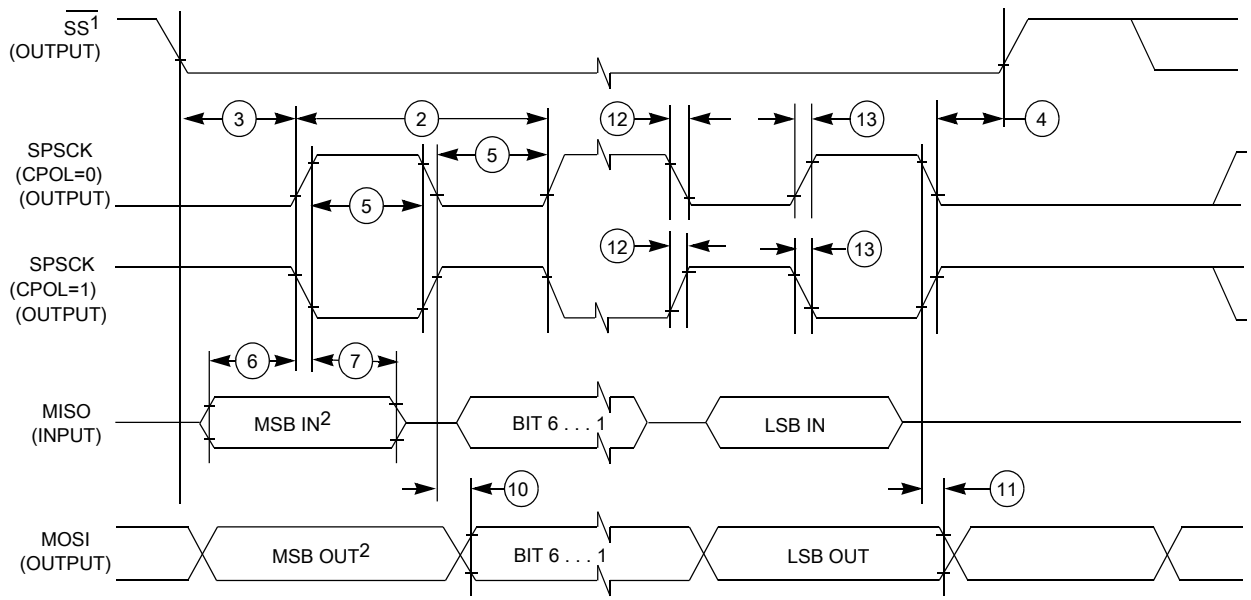


Figure 14. Typical hysteresis vs. Vin level (VDDA = 3.3 V, PMODE = 0)

Table 29. LPSPI electrical specifications[1]

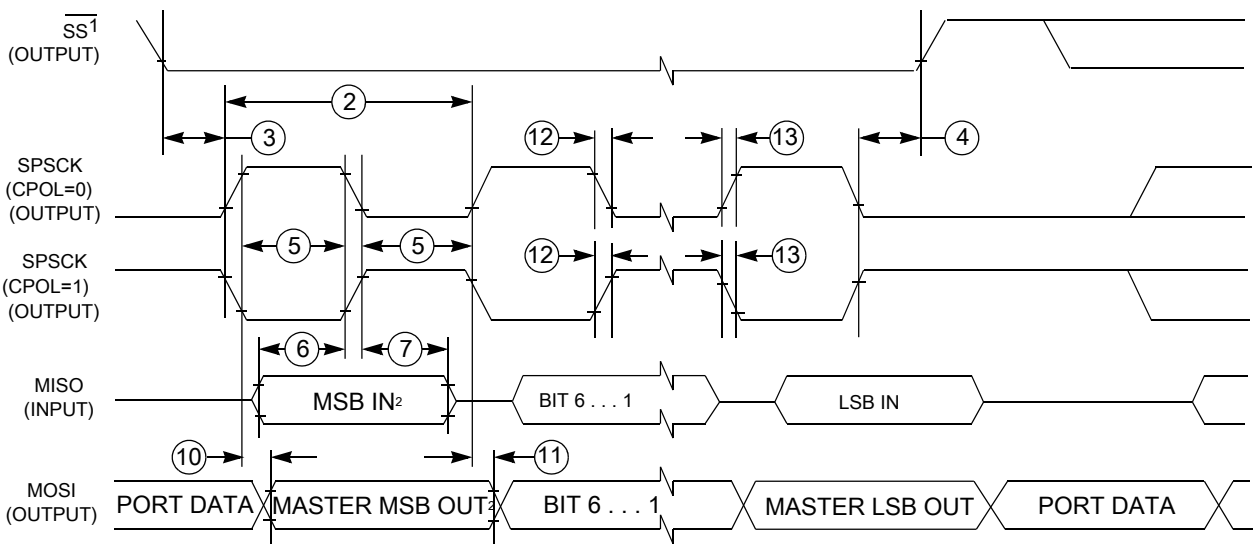
Num	Symbol	Description	Conditions	Run Mode[2]				HSRUN Mode[2]				VLPR Mode				Unit
				5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
	f_{periph} [3, 4]	Peripheral Frequency	Slave	-	40	-	40	-	56	-	56	-	8	-	8	MHz
			Master	-	40	-	40	-	56	-	56	-	8	-	8	
			Master Loopback [5]	-	40	-	48	-	48	-	48	-	8	-	8	
			Master Loopback(Slow) [6]	-	48	-	48	-	48	-	48	-	8	-	8	
1	f_{op}	Frequency of operation	Slave	-	10	-	10	-	14	-	14	-	4	-	4	MHz
			Master	-	10	-	10	-	14	-	14	-	4	-	4	
			Master Loopback[5]	-	20	-	12	-	24	-	12	-	4	-	4	
			Master Loopback(slow) [6]	-	12	-	12	-	12	-	12	-	4	-	4	
2	t_{SPSCK}	SPSCK period	Slave	100	-	100	-	72	-	72	-	250	-	250	-	ns
			Master	100	-	100	-	72	-	72	-	250	-	250	-	
			Master Loopback[5]	50	-	83	-	42	-	83	-	250	-	250	-	
			Master Loopback(slow) [6]	83	-	83	-	83	-	83	-	250	-	250	-	
3	t_{Lead}[7]	Enable lead time (PCS to SPSCK delay)	Slave	-	-	-	-	-	-	-	-	-	-	-	-	ns

Table continues on the next page...



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 18. LPSPI master mode timing (CPHA = 0)



1.If configured as output
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 19. LPSPI master mode timing (CPHA = 1)

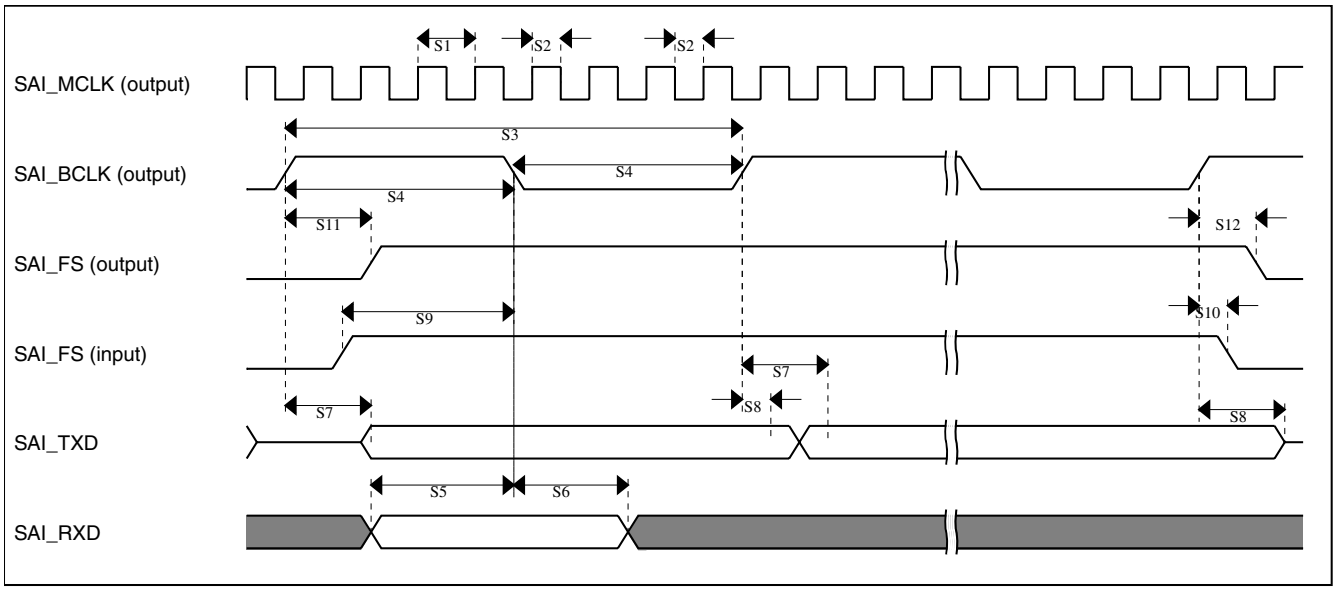


Figure 22. SAI Timing — Master modes

Table 31. Slave mode timing specifications

Symbol	Description	Min.	Max.	Unit
—	Operating voltage	2.97	3.6	V
S13	SAI_BCLK cycle time (input)	80	—	ns
S14[1]	SAI_BCLK pulse width high/low (input)	45%	55%	BCLK period
S15	SAI_RXD input setup before SAI_BCLK	8	—	ns
S16	SAI_RXD input hold after SAI_BCLK	2	—	ns
S17	SAI_BCLK to SAI_TXD output valid	—	28	ns
S18	SAI_BCLK to SAI_TXD output invalid	0	—	ns
S19	SAI_FS input setup before SAI_BCLK	8	—	ns
S20	SAI_FS input hold after SAI_BCLK	2	—	ns
S21	SAI_BCLK to SAI_FS output valid	—	28	ns
S22	SAI_BCLK to SAI_FS output invalid	0	—	ns

1. The slave mode parameters (S15 - S22) assume 50% duty cycle on SAI_BCLK input. Any change in SAI_BCLK duty cycle input must be taken care during the board design or by the master timing.

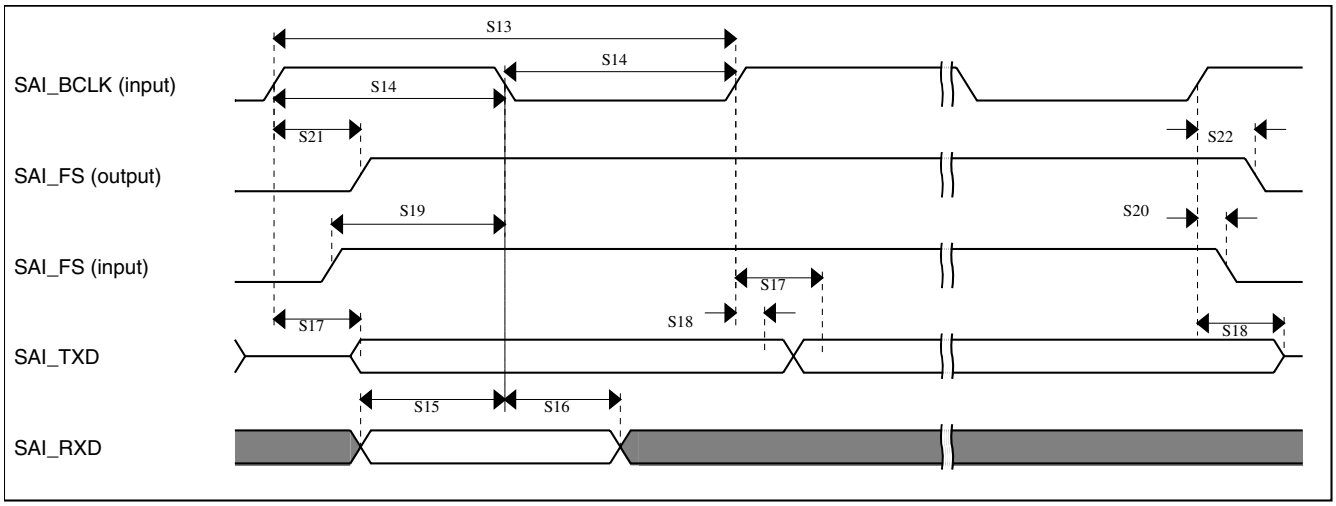


Figure 23. SAI Timing — Slave modes

6.5.6 Ethernet AC specifications

The following timing specs are defined at the chip I/O pin and must be translated appropriately to arrive at timing specs/constraints for the physical interface.

The following table describes the MII electrical characteristics.

- Measurements are with maximum output load of 25 pF, input transition of 1 ns and pad configured with fastest slew settings (DSE = 1'b1).
- I/O operating voltage ranges from 2.97 V to 3.6 V
- While doing the mode transition (RUN -> HSRUN or HSRUN -> RUN), the interface should be OFF.

Table 32. MII signal switching specifications

Symbol	Description	Min.	Max.	Unit
—	RXCLK frequency	—	25	MHz
MII1	RXCLK pulse width high	35%	65%	RXCLK period
MII2	RXCLK pulse width low	35%	65%	RXCLK period
MII3	RXD[3:0], RXDV, RXER to RXCLK setup	5	—	ns
MII4	RXCLK to RXD[3:0], RXDV, RXER hold	5	—	ns
—	TXCLK frequency	—	25	MHz
MII5	TXCLK pulse width high	35%	65%	TXCLK period
MII6	TXCLK pulse width low	35%	65%	TXCLK period
MII7	TXCLK to TXD[3:0], TXEN, TXER invalid	2	—	ns
MII8	TXCLK to TXD[3:0], TXEN, TXER valid	—	25	ns

Table 37. JTAG electrical specifications

Symbol	Description	Run Mode				HSRUN Mode				VLPR Mode				Unit
		5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		5.0 V IO		3.3 V IO		
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
JI	TCLK frequency of operation													MHz
	Boundary Scan	-	20	-	20	-	20	-	20	-	10	-	10	
	JTAG	-	20	-	20	-	20	-	20	-	10	-	10	
J2	TCLK cycle period	1/JI	-	1/JI	-	1/JI	-	1/JI	-	1/JI	-	1/JI	-	ns
J3	TCLK clock pulse width													ns
	Boundary Scan	J2/2 - 5	J2/2 + 5	J2/2 - 5	J2/2 + 5	J2/2 - 5	J2/2 + 5	J2/2 - 5	J2/2 + 5	J2/2 - 5	J2/2 + 5	J2/2 - 5	J2/2 + 5	
	JTAG													
J4	TCLK rise and fall times	-	1	-	1	-	1	-	1	-	1	-	1	ns
J5	Boundary scan input data setup time to TCLK rise	5	-	5	-	5	-	5	-	15	-	15	-	ns
J6	Boundary scan input data hold time after TCLK rise	5	-	5	-	5	-	5	-	8	-	8	-	ns
J7	TCLK low to boundary scan output data valid	-	28	-	32	-	28	-	32	-	80	-	80	ns
J8	TCLK low to boundary scan output data invalid	0	-	0	-	0	-	0	-	0	-	0	-	
J9	TCLK low to boundary scan output high-Z	-	28	-	32	-	28	-	32	-	80	-	80	ns
J10	TMS, TDI input data setup time to TCLK rise	3	-	3	-	3	-	3	-	15	-	15	-	ns
J11	TMS, TDI input data hold time after TCLK rise	2	-	2	-	2	-	2	-	8	-	8	-	ns
J12	TCLK low to TDO data valid	-	28	-	32	-	28	-	32	-	80	-	80	ns
J13	TCLK low to TDO data invalid	0	-	0	-	0	-	0	-	0	-	0	-	ns
J14	TCLK low to TDO high-Z	-	28	-	32	-	28	-	32	-	80	-	80	ns

Table 40. Revision History (continued)

Rev. No.	Date	Substantial Changes
		• Updated values for V_{REFH} and V_{REFL} to add refernce to the section "voltage and current operating requirments" for Min and Max valaues • Updated footnote to Typ. • Removed footnote from RAS Analog source resistance • Updated figure: ADC input impedance equivalency diagram • In table: 12-bit ADC characteristics (2.7 V to 3 V) (V_{REFH} = V_{DDA}, V_{REFL} = V_{SS}) • Removed rows for V_{TEMP_S} and V_{TEMP25} • Updated footnote to Typ. • In table: 12-bit ADC characteristics (3 V to 5.5 V)(V_{REFH} = V_{DDA}, V_{REFL} = V_{SS}) • Removed rows for V_{TEMP_S} and V_{TEMP25} • Removed number for TUE • Updated footnote to Typ. • In table: Comparator with 8-bit DAC electrical specifications • Updated Typ. of I_{DDLS} Supply current, Low-speed mode • Updated Typ. of t_{DLSB} Propagation delay, Low-speed mode • Updated Typ. of t_{DHSS} Propagation delay, High-speed mode • Updated t_{DLSS} Propagation delay • Added row for t_{DDAC} Initialization and switching settling time • Updated footnote • Updated section LPSPI electrical specifications • Added section: SAI electrical specifications • Updated section: Ethernet AC specifications • Added section: Clockout frequency • Added section: Trace electrical specifications • Updated table: Table 38 : Updated numbers for S32K142 and S32K148 • Updated table: Table 39 : Updated numbers for S32K148 • Updated Document number for 32-pin QFN in topic Obtaining package dimensions
3	14 March 2017	• In Table 2 • Updated min. value of V_{DD_OFF} • Added parameter I_{INJSUM_AF} • Updated Power mode transition operating behaviors • Updated Power consumption • Updated footnote to T_{SPLL_LOCK} in SPLL electrical specifications • In 12-bit ADC electrical characteristics • Updated table: 12-bit ADC characteristics (2.7 V to 3 V) (VREFH = VDDA, VREFL = VSS) • Added typ. value to I_{DDA_ADC}, TUE, DNL, and INL • Added min. value to SMPLTS • Removed footnote 'All the parameters in this table ... ' • Updated table: 12-bit ADC characteristics (3 V to 5.5 V) (VREFH = VDDA, VREFL = VSS) • Added typ. value to I_{DDA_ADC} • Removed footnote 'All the parameters in this table ... ' • In Table 21 updated Max. value of t_{vfykey} to 33 µs
4	02 June 2017	• In section: Block diagram, added block diagram for S32K11x series. • Updated figure: S32K1xx product series comparison. • In section: Determining valid orderable parts , added reference to attachement *S32K_Part_Numbers.xlsx*. • In section: Ordering information • Updated figure: Ordering information. • In Table 1,

How to Reach Us:

Home Page:
nxp.com

Web Support:
nxp.com/support

Document Number S32K1XX
Revision 4, 06/2017